Erik Janzen

List of Publications by Year
in descending order

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629	15,760	19636 61	38368 95
papers	citations	h-index	g-index

632	632	632	7240
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Coherent control of single spins in silicon carbide at room temperature. Nature Materials, 2015, 14, 164-168.	13.3	472
2	Isolated electron spins in silicon carbide with millisecond coherence times. Nature Materials, 2015, 14, 160-163.	13.3	362
3	Accurate defect levels obtained from the HSE06 range-separated hybrid functional. Physical Review B, 2010, 81, .	1.1	297
4	Deep level defects in electron-irradiated 4H SiC epitaxial layers. Journal of Applied Physics, 1997, 81, 6155-6159.	1.1	279
5	Deep levels created by low energy electron irradiation in 4H-SiC. Journal of Applied Physics, 2004, 96, 4909-4915.	1.1	247
6	High-resolution studies of sulfur- and selenium-related donor centers in silicon. Physical Review B, 1984, 29, 1907-1918.	1.1	240
7	Silicon vacancy related defect in 4H and 6H SiC. Physical Review B, 2000, 61, 2613-2620.	1.1	223
8	Negative-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>U</mml:mi></mml:math>System of Carbon Vacancy in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:math>-SiC. Physical Review Letters, 2012, 109, 187603.	2.9	219
9	Theory of Spin-Conserving Excitation of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>N</mml:mi><mml:mo>â^'</mml:mo><mml:msup><mml:mi>V</mml:mi><mml:mo>â^'</mml:mo></mml:msup in Diamond. Physical Review Letters, 2009, 103, 186404.	2.9	206
10	Electronic structure of the GaAs:MnGascenter. Physical Review B, 1997, 55, 6938-6944.	1.1	187
11	Divacancy in 4H-SiC. Physical Review Letters, 2006, 96, 055501.	2.9	172
12	Electrically active defects inn-type 4Hâ€"silicon carbide grown in a vertical hot-wall reactor. Journal of Applied Physics, 2003, 93, 4708-4714.	1.1	169
13	Influence of epitaxial growth and substrate-induced defects on the breakdown of 4Hâ€"SiC Schottky diodes. Applied Physics Letters, 2000, 76, 2725-2727.	1.5	163
14	Photoluminescence studies of porous silicon carbide. Applied Physics Letters, 1995, 66, 2250-2252.	1.5	137
15	Tellurium donors in silicon. Physical Review B, 1981, 24, 4571-4586.	1.1	136
16	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide. Nano Letters, 2017, 17, 1782-1786.	4.5	129
17	Isolated Spin Qubits in SiC with a High-Fidelity Infrared Spin-to-Photon Interface. Physical Review X, 2017, 7, .	2.8	125
18	Growth of SiC by ?Hot-Wall? CVD and HTCVD. Physica Status Solidi (B): Basic Research, 1997, 202, 321-334.	0.7	121

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19	A 4.5 kV 6H silicon carbide rectifier. Applied Physics Letters, 1995, 67, 1561-1563.	1.5	119
20	Removal of polishing-induced damage from 6H-SiC(0001) substrates by hydrogen etching. Journal of Crystal Growth, 1996, 167, 391-395.	0.7	118
21	Luminescence from stacking faults in 4H SiC. Applied Physics Letters, 2001, 79, 3944-3946.	1.5	118
22	In situ substrate preparation for high-quality SiC chemical vapour deposition. Journal of Crystal Growth, 1997, 181, 241-253.	0.7	112
23	High temperature chemical vapor deposition of SiC. Applied Physics Letters, 1996, 69, 1456-1458.	1.5	111
24	Electron effective masses in 4H SiC. Applied Physics Letters, 1995, 66, 1074-1076.	1.5	109
25	Ab initiodensity-functional supercell calculations of hydrogen defects in cubic SiC. Physical Review B, 2001, 63, .	1.1	109
26	Electrical properties and formation mechanism of porous silicon carbide. Applied Physics Letters, 1994, 65, 2699-2701.	1.5	103
27	Aggregation of carbon interstitials in silicon carbide: A theoretical study. Physical Review B, 2003, 68, .	1.1	103
28	Chloride-Based CVD Growth of Silicon Carbide for Electronic Applications. Chemical Reviews, 2012, 112, 2434-2453.	23.0	99
29	Deep sulfurâ€related centers in silicon. Journal of Applied Physics, 1980, 51, 4212-4217.	1.1	98
30	Carbon vacancy-related defect in 4Hand 6HSiC. Physical Review B, 2001, 63, .	1.1	98
31	Nitrogen doping concentration as determined by photoluminescence in 4Hâ€“ and 6Hâ€“SiC. Journal of Applied Physics, 1996, 80, 3504-3508.	1.1	96
32	Dislocation evolution in 4H-SiC epitaxial layers. Journal of Applied Physics, 2002, 91, 6354.	1.1	96
33	Electronic properties of seleniumâ€doped silicon. Journal of Applied Physics, 1980, 51, 3740-3745.	1.1	94
34	The silicon vacancy in SiC. Physica B: Condensed Matter, 2009, 404, 4354-4358.	1.3	91
35	Properties and origins of different stacking faults that cause degradation in SiC PiN diodes. Journal of Applied Physics, 2004, 95, 1485-1488.	1.1	90
36	Investigation of the interface between silicon nitride passivations and AlGaN/AlN/GaN heterostructures by C(V) characterization of metal-insulator-semiconductor-heterostructure capacitors. Journal of Applied Physics, 2010, 108, .	1.1	90

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37	Pseudodonor nature of the DI defect in 4H-SiC. Applied Physics Letters, 2001, 78, 46-48.	1.5	88
38	Growth rate predictions of chemical vapor deposited silicon carbide epitaxial layers. Journal of Crystal Growth, 2002, 243, 170-184.	0.7	88
39	Very high growth rate of 4H-SiC epilayers using the chlorinated precursor methyltrichlorosilane (MTS). Journal of Crystal Growth, 2007, 307, 334-340.	0.7	83
40	Electronic structure of the neutral silicon vacancy in4Hand6HSiC. Physical Review B, 2000, 62, 16555-16560.	1.1	82
41	Electron effective masses and mobilities in highâ€purity 6Hâ€“SiC chemical vapor deposition layers. Applied Physics Letters, 1994, 65, 3209-3211.	1.5	80
42	Properties of theD1bound exciton in4Hâˆ’SiC. Physical Review B, 1999, 59, 1956-1963.	1.1	80
43	Multivalley spin splitting of1sstates for sulfur, selenium, and tellurium donors in silicon. Physical Review B, 1982, 25, 2627-2632.	1.1	77
44	Determination of the electron effective-mass tensor in 4HSiC. Physical Review B, 1996, 53, 15409-15412.	1.1	77
45	Techniques for Minimizing the Basal Plane Dislocation Density in SiC Epilayers to Reduce V_f Drift in SiC Bipolar Power Devices. Materials Science Forum, 2006, 527-529, 141-146.	0.3	76
46	Impact of residual carbon on two-dimensional electron gas properties in AlxGa1âˆ’xN/GaN heterostructure. Applied Physics Letters, 2013, 102, .	1.5	76
47	Structural macro-defects in 6H-SiC wafers. Journal of Crystal Growth, 1993, 132, 504-512.	0.7	75
48	The minority carrier lifetime of nâ€type 4Hâ€and 6Hâ€SiC epitaxial layers. Applied Physics Letters, 1996, 69, 679-681.	1.5	74
49	High temperature CVD growth of SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 113-120.	1.7	73
50	A 3 kV Schottky barrier diode in 4H-SiC. Applied Physics Letters, 1998, 72, 445-447.	1.5	72
51	Correlation between the antisite pair and theDIcenter in SiC. Physical Review B, 2003, 67, .	1.1	72
52	Identification of the Carbon Antisite-Vacancy Pair in4H-SiC. Physical Review Letters, 2006, 96, 145501.	2.9	72
53	Growth of 6H and 4Hâ€“SiC by sublimation epitaxy. Journal of Crystal Growth, 1999, 197, 155-162.	0.7	71
54	Photoexcitation-electron-paramagnetic-resonance studies of the carbon vacancy in 4H-SiC. Applied Physics Letters, 2002, 81, 3945-3947.	1.5	70

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55	Structural defects in electrically degraded 4H-SiC p+/nâˆ’/n+ diodes. Applied Physics Letters, 2002, 80, 4852-4854.	1.5	69
56	Thick Silicon Carbide Homoepitaxial Layers Grown by CVD Techniques. Chemical Vapor Deposition, 2006, 12, 475-482.	1.4	69
57	Fast chemical sensing with metal-insulator silicon carbide structures. IEEE Electron Device Letters, 1997, 18, 287-289.	2.2	68
58	Nitrogen doping of epitaxial silicon carbide. Journal of Crystal Growth, 2002, 236, 101-112.	0.7	66
59	Vector Magnetometry Using Silicon Vacancies in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:math>-SiC Under Ambient Conditions. Physical Review Applied, 2016, 6, .	1.5	66
60	Liquid phase epitaxial growth of SiC. Journal of Crystal Growth, 1999, 197, 147-154.	0.7	65
61	Photoluminescence of electron-irradiated4Hâˆ’SiC. Physical Review B, 1999, 59, 8008-8014.	1.1	64
62	Direct generation of linearly polarized photon emission with designated orientations from site-controlled InGaN quantum dots. Light: Science and Applications, 2014, 3, e139-e139.	7.7	63
63	Time Resolved Spectroscopy of Defects in SiC. Physica Status Solidi A, 1997, 162, 65-77.	1.7	61
64	Current status and advances in the growth of SiC. Diamond and Related Materials, 2000, 9, 432-438.	1.8	61
65	Fano resonances in chalcogen-doped silicon. Physical Review B, 1985, 31, 8000-8012.	1.1	60
66	Defects and carrier compensation in semi-insulating4Hâˆ’SiCsubstrates. Physical Review B, 2007, 75, .	1.1	60
67	EPR identification of intrinsic defects in SiC. Physica Status Solidi (B): Basic Research, 2008, 245, 1298-1314.	0.7	60
68	On-axis homoepitaxial growth on Si-face 4Hâ€“SiC substrates. Journal of Crystal Growth, 2008, 310, 4424-4429.	0.7	60
69	Polytype stability in seeded sublimation growth of 4Hâ€“SiC boules. Journal of Crystal Growth, 2000, 217, 255-262.	0.7	59
70	Aluminum doping of epitaxial silicon carbide. Journal of Crystal Growth, 2003, 253, 340-350.	0.7	59
71	Reducing Thermal Resistance of AlGaN/GaN Electronic Devices Using Novel Nucleation Layers. IEEE Electron Device Letters, 2009, 30, 103-106.	2.2	59
72	Effective mass of electron in monolayer graphene: Electron-phonon interaction. Journal of Applied Physics, 2013, 113, .	1.1	59

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73	Theoretical model of dynamic spin polarization of nuclei coupled to paramagnetic point defects in diamond and silicon carbide. Physical Review B, 2015, 92, .	1.1	59
74	Dispersive Effects in Microwave AlGaN/AlN/GaN HEMTs With Carbon-Doped Buffer. IEEE Transactions on Electron Devices, 2015, 62, 2162-2169.	1.6	59
75	Resonant optical spectroscopy and coherent control of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">C</mml:mi><mml:msup><mml:mrow><mml:mi mathvariant="normal">r</mml:mi></mml:mrow><mml:mrow><mml:mn>4</mml:mn><mml:mo>+</mml:mo></mml:mrow></mml:msup ensembles in SiC and GaN. Physical Review B, 2017, 95, .	1.1	59
76	Defects in High-Purity Semi-Insulating SiC. Materials Science Forum, 2004, 457-460, 437-442.	0.3	57
77	SiC Crystal Growth by HTCVD. Materials Science Forum, 2004, 457-460, 9-14.	0.3	56
78	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. Applied Physics Letters, 2013, 102, .	1.5	56
79	A GaNâ€“SiC hybrid material for high-frequency and power electronics. Applied Physics Letters, 2018, 113, .	1.5	56
80	EPR and theoretical studies of negatively charged carbon vacancy in4Hâˆ'SiC. Physical Review B, 2005, 71, .	1.1	55
81	Single Excitons in InGaN Quantum Dots on GaN Pyramid Arrays. Nano Letters, 2011, 11, 2415-2418.	4.5	54
82	Growth of 3CSiC on on-axis Si(100) substrates by chemical vapor deposition. Journal of Crystal Growth, 1995, 154, 303-314.	0.7	53
83	Capture cross sections of electron irradiation induced defects in 6Hâ€“SiC. Journal of Applied Physics, 1998, 84, 704-708.	1.1	53
84	Step-bunching in SiC epitaxy: anisotropy and influence of growth temperature. Journal of Crystal Growth, 2002, 236, 297-304.	0.7	53
85	HTCVD Grown Semi-Insulating SiC Substrates. Materials Science Forum, 2003, 433-436, 33-38.	0.3	52
86	High quality 4Hâ€SiC epitaxial layers grown by chemical vapor deposition. Applied Physics Letters, 1995, 66, 1373-1375.	1.5	50
87	Doping-induced strain in N-doped 4Hâ€“SiC crystals. Applied Physics Letters, 2003, 82, 3689-3691.	1.5	50
88	EPR and theoretical studies of positively charged carbon vacancy in 4H-SiC. Physical Review B, 2004, 70, .	1.1	50
89	Spin and photophysics of carbon-antisite vacancy defect in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:mrow></mml: carbide: A potential quantum bit. Physical Review B, 2015, 91, .	1.1	50
90	Shallow donor and DX states of Si in AlN. Applied Physics Letters, 2011, 98, .	1.5	49

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91	High-quality AlN layers grown by hot-wall MOCVD at reduced temperatures. Journal of Crystal Growth, 2012, 338, 52-56.	0.7	49
92	Layer-number determination in graphene on SiC by reflectance mapping. Carbon, 2014, 77, 492-500.	5.4	48
93	Stable and metastable Si negative-U centers in AlGaN and AlN. Applied Physics Letters, 2014, 105, .	1.5	47
94	Electronic properties of Si-doped Al<i>x</i>Ga1â^'xN with aluminum mole fractions above 80%. Journal of Applied Physics, 2016, 120, .	1.1	47
95	Epitaxial growth of SiC in a chimney CVD reactor. Journal of Crystal Growth, 2002, 236, 225-238.	0.7	46
96	Theoretical unification of hybrid-DFT and<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mtext>DFT</mml:mtext><mml:mo>â€‰</mml:mo><mml:mo[illegible]</mml:mo for the treatment of localized orbitals. Physical Review B, 2014, 90, .	1.1	46
97	Improved morphology for epitaxial growth on 4Â° off-axis 4H-SiC substrates. Journal of Crystal Growth, 2009, 311, 3265-3272.	0.7	45
98	Negative-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>U</mml:mi></mml:math>carbon vacancy in 4<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>H</mml:mi></mml:math>-SiC: Assessment of charge correction schemes and identification of the negative carbon vacancy at the quasicubic site. Physical Review B, 2013, 88, .	1.1	45
99	Crystalline imperfections in 4H SiC grown with a seeded Lely method. Journal of Crystal Growth, 1994, 144, 267-276.	0.7	44
100	Heat Capacity of 4H-SiC Determined by Differential Scanning Calorimetry. Journal of the Electrochemical Society, 2000, 147, 3546.	1.3	44
101	Optical Characterization of Deep Level Defects in SiC. Materials Science Forum, 2005, 483-485, 341-346.	0.3	44
102	Hot-Wall MOCVD for Highly Efficient and Uniform Growth of AlN. Crystal Growth and Design, 2009, 9, 880-884.	1.4	44
103	Temperature dependent effective mass in AlGaN/GaN high electron mobility transistor structures. Applied Physics Letters, 2012, 101, .	1.5	44
104	Direct observation of intercenter charge transfer in dominant nonradiative recombination channels in silicon. Physical Review Letters, 1991, 67, 1914-1917.	2.9	43
105	Ligand hyperfine interaction at the neutral silicon vacancy in 4H- and6Hâ^'SiC. Physical Review B, 2002, 66, .	1.1	43
106	Identification of the gallium vacancyâ€"oxygen pair defect in GaN. Physical Review B, 2009, 80, .	1.1	43
107	Room-temperature mobility above 2200â€‰cm2/VÂ·s of two-dimensional electron gas in a sharp-interface AlGaN/GaN heterostructure. Applied Physics Letters, 2015, 106, .	1.5	43
108	Characterisation and Defects in Silicon Carbide. Materials Science Forum, 2002, 389-393, 9-14.	0.3	42

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109	Annealing behavior of the carbon vacancy in electron-irradiated 4H-SiC. Journal of Applied Physics, 2004, 96, 2406-2408.	1.1	42
110	AlGaInN metal-organic-chemical-vapor-deposition gas-phase chemistry in hydrogen and nitrogen diluents: First-principles calculations. Chemical Physics Letters, 2006, 431, 346-351.	1.2	42
111	Growth of highâ€quality 3Câ€SiC epitaxial films on offâ€axis Si(001) substrates at 850â€‰Â°C by reactive magnetron sputtering. Applied Physics Letters, 1994, 65, 725-727.	1.5	41
112	Intrinsic Defects in Silicon Carbide Polytypes. Materials Science Forum, 2001, 353-356, 499-504.	0.3	41
113	Observation of rapid direct charge transfer between deep defects in silicon. Physical Review Letters, 1994, 72, 2939-2942.	2.9	40
114	Effect of impurity incorporation on crystallization in AlN sublimation epitaxy. Journal of Applied Physics, 2004, 96, 5293-5297.	1.1	40
115	In-situ surface preparation of nominally on-axis 4H-SiC substrates. Journal of Crystal Growth, 2008, 310, 4430-4437.	0.7	40
116	Phonon replicas at theMpoint in4Hâ^'SiC:A theoretical and experimental study. Physical Review B, 1998, 58, 13634-13647.	1.1	39
117	Quantitative comparison between Z1â^•2 center and carbon vacancy in 4H-SiC. Journal of Applied Physics, 2014, 115, .	1.1	39
118	Capture processes at double donors in silicon. Physical Review B, 1985, 31, 3659-3666.	1.1	38
119	Optically detected magnetic resonance studies of defects in electron-irradiated 3C SiC layers. Physical Review B, 1997, 55, 2863-2866.	1.1	38
120	The origin of 3C polytype inclusions in epitaxial layers of silicon carbide grown by chemical vapour deposition. Diamond and Related Materials, 1997, 6, 1297-1300.	1.8	38
121	The mechanism for cubic SiC formation on off-oriented substrates. Journal of Crystal Growth, 1997, 178, 495-504.	0.7	38
122	Electrical characterization of metastable carbon clusters inSiC: A theoretical study. Physical Review B, 2006, 73, .	1.1	38
123	Thick homoepitaxial layers grown on on-axis Si-face 6H- and 4H-SiC substrates with HCl addition. Journal of Crystal Growth, 2009, 312, 24-32.	0.7	38
124	Interface chemistry and electric characterisation of nickel metallisation on 6Hî—¸SiC. Applied Surface Science, 1996, 99, 119-125.	3.1	37
125	Improved hot-wall MOCVD growth of highly uniform AlGaN/GaN/HEMT structures. Journal of Crystal Growth, 2009, 311, 3007-3010.	0.7	37
126	Long minority carrier lifetimes in 6H SiC grown by chemical vapor deposition. Applied Physics Letters, 1995, 66, 189-191.	1.5	36

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127	Preferential etching of SiC crystals. Diamond and Related Materials, 1997, 6, 1456-1458.	1.8	36
128	Photoluminescence and Zeeman effect in chromium-doped 4H and 6H SiC. Journal of Applied Physics, 1999, 86, 4348-4353.	1.1	36
129	Investigation of deep levels in bulk GaN material grown by halide vapor phase epitaxy. Journal of Applied Physics, 2013, 114, .	1.1	36
130	Timeâ€resolved decay of the blue emission in porous silicon. Applied Physics Letters, 1994, 65, 2451-2453.	1.5	35
131	Photoluminescence determination of the nitrogen doping concentration in 6Hâ€SiC. Applied Physics Letters, 1994, 65, 2457-2459.	1.5	35
132	Observation of negative-U centers in 6H silicon carbide. Applied Physics Letters, 1999, 74, 839-841.	1.5	35
133	Silicon Antisite in4HSiC. Physical Review Letters, 2001, 87, 045502.	2.9	35
134	Role of screening in the density functional applied to transition-metal defects in semiconductors. Physical Review B, 2013, 87, .	1.1	35
135	Direct current magnetron sputtered ZrB2 thin films on 4H-SiC(0001) and Si(100). Thin Solid Films, 2014, 550, 285-290.	0.8	35
136	Chemical identification of deep energy levels in Si:Se. Journal of Applied Physics, 1980, 51, 6238-6242.	1.1	34
137	Improved Ni ohmic contact on n-type 4H-SiC. Journal of Electronic Materials, 1997, 26, 119-122.	1.0	34
138	Group-II acceptors in wurtzite AlN: A screened hybrid density functional study. Applied Physics Letters, 2010, 96, .	1.5	34
139	Fast SiC Epitaxial Growth in a Chimney CVD Reactor and HTCVD Crystal Growth Developments. Materials Science Forum, 2000, 338-342, 131-136.	0.3	33
140	Nitrogen incorporation during 4H-SiC epitaxy in a chimney CVD reactor. Journal of Crystal Growth, 2001, 226, 267-276.	0.7	33
141	Morphology Control of Hot-Wall MOCVD Selective Area Grown Hexagonal GaN Pyramids. Crystal Growth and Design, 2012, 12, 5491-5496.	1.4	33
142	Graphene self-switching diodes as zero-bias microwave detectors. Applied Physics Letters, 2015, 106, .	1.5	33
143	Stoichiometric, epitaxial ZrB2 thin films with low oxygen-content deposited by magnetron sputtering from a compound target: Effects of deposition temperature and sputtering power. Journal of Crystal Growth, 2015, 430, 55-62.	0.7	33
144	Ga-bound excitons in 3C-, 4H-, and 6H-SiC. Physical Review B, 1996, 53, 13503-13506.	1.1	32

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145	Effect of vapor composition on polytype homogeneity of epitaxial silicon carbide. Journal of Applied Physics, 1996, 80, 5704-5712.	1.1	32
146	Barrier height determination for n-type 4H-SiC schottky contacts made using various metals. Journal of Electronic Materials, 1998, 27, 871-875.	1.0	32
147	Growth characteristics of chlorideâ€based SiC epitaxial growth. Physica Status Solidi - Rapid Research Letters, 2008, 2, 278-280.	1.2	32
148	Precursors for carbon doping of GaN in chemical vapor deposition. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	0.6	32
149	The material quality of CVD-grown SiC using different carbon precursors. Journal of Crystal Growth, 1998, 183, 163-174.	0.7	31
150	Analysis of the sharp donor-acceptor pair luminescence in4H-SiC doped with nitrogen and aluminum. Physical Review B, 2003, 67, .	1.1	31
151	Electron paramagnetic resonance and theoretical studies of shallow phosphorous centers in3C-,4H-, and6Hâ^'SiC. Physical Review B, 2006, 73, .	1.1	31
152	All-optical characterization of carrier lifetimes and diffusion lengths in MOCVD-, ELO-, and HVPE-grown GaN. Journal of Crystal Growth, 2007, 300, 223-227.	0.7	31
153	Theory of Neutral Divacancy in SiC: A Defect for Spintronics. Materials Science Forum, 0, 645-648, 395-397.	0.3	31
154	High thermal stability quasi-free-standing bilayer graphene formed on 4Hâ€"SiC(0 0 0 1) via platinum intercalation. Carbon, 2014, 79, 631-635.	5.4	31
155	Capture, emission and recombination at a deep level via an excited state. Journal of Physics C: Solid State Physics, 1980, 13, 6157-6165.	1.5	30
156	Dominant recombination center in electronâ€irradiated 3CSiC. Journal of Applied Physics, 1996, 79, 3784-3786.	1.1	30
157	SiC material for high-power applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 46, 203-209.	1.7	30
158	Thickness determination of low doped SiC epi-films on highly doped SiC substrates. Journal of Electronic Materials, 1998, 27, 300-303.	1.0	30
159	Optically detected magnetic resonance studies of intrinsic defects in 6H-SiC. Semiconductor Science and Technology, 1999, 14, 1141-1146.	1.0	30
160	Electrical Activity of Residual Boron in Silicon Carbide. Materials Science Forum, 2002, 389-393, 549-552.	0.3	30
161	Defects in Semi-Insulating SiC Substrates. Materials Science Forum, 2003, 433-436, 45-50.	0.3	30
162	Uniform hot-wall MOCVD epitaxial growth of 2inch AlGaN/GaN HEMT structures. Journal of Crystal Growth, 2007, 300, 100-103.	0.7	30

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163	Clustering of vacancy defects in high-purity semi-insulating SiC. Physical Review B, 2007, 75, .	1.1	30
164	The complex impact of silicon and oxygen on the n-type conductivity of high-Al-content AlGaN. Applied Physics Letters, 2013, 102, .	1.5	30
165	Electron effective mass in Al0.72Ga0.28N alloys determined by mid-infrared optical Hall effect. Applied Physics Letters, 2013, 103, .	1.5	30
166	The determination of high-density carrier plasma parameters in epitaxial layers, semi-insulating and heavily doped crystals of 4H-SiC by a picosecond four-wave mixing technique. Semiconductor Science and Technology, 2006, 21, 952-958.	1.0	29
167	Low thermal resistance of a GaN-on-SiC transistor structure with improved structural properties at the interface. Journal of Crystal Growth, 2015, 428, 54-58.	0.7	29
168	SiC â€“ a semiconductor for high-power, high-temperature and high-frequency devices. Physica Scripta, 1994, T54, 283-290.	1.2	28
169	Carbon-vacancy related defects in 4H- and 6H-SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 202-206.	1.7	28
170	Micropipe Healing in Liquid Phase Epitaxial Growth of SiC. Materials Science Forum, 2000, 338-342, 237-240.	0.3	28
171	Material characterization need for SiC-based devices. Materials Science in Semiconductor Processing, 2001, 4, 181-186.	1.9	28
172	Possible lifetimeâ€limiting defect in 6H SiC. Applied Physics Letters, 1994, 65, 2687-2689.	1.5	27
173	Impurity-controlled dopant activation: Hydrogen-determined site selection of boron in silicon carbide. Applied Physics Letters, 2001, 79, 2746-2748.	1.5	27
174	Cathodoluminescence identification of donorâ€“acceptor related emissions in as-grown 4Hâ€“SiC layers. Journal of Applied Physics, 2002, 91, 2890-2895.	1.1	27
175	Predicted nitrogen doping concentrations in silicon carbide epitaxial layers grown by hot-wall chemical vapor deposition. Journal of Crystal Growth, 2003, 250, 471-478.	0.7	27
176	Optically detected cyclotron resonance investigations on4Hand6HSiC: Band-structure and transport properties. Physical Review B, 2000, 61, 4844-4849.	1.1	26
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